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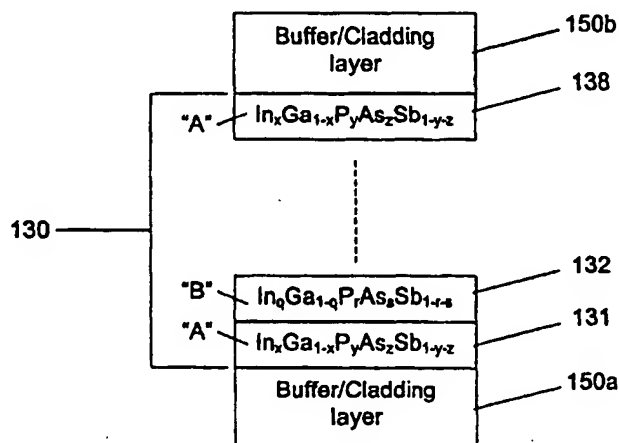
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(54) Title: COMPOUND SEMICONDUCTOR STRUCTURES FOR OPTOELECTRONIC DEVICES



(57) Abstract

A compound semiconductor device is provided that includes a substrate and an active region disposed above the substrate. The active region includes at least two different pseudomorphic layers, the first layer having the form $\text{In}_x\text{Ga}_{1-x}\text{P}_y\text{As}_z\text{Sb}_{1-y-z}$, and the second layer having the form $\text{In}_q\text{Ga}_{1-q}\text{P}_r\text{As}_s\text{Sb}_{1-r-s}$. The first layer includes at least In, Ga, and As, and the second layer includes at least Ga, As, and Sb. It is preferable for the substrate to be GaAs or $\text{Al}_p\text{Ga}_{1-p}\text{As}$ ($0 < p < 1$), or to have a lattice constant close to or equal to that of GaAs. For the first layer, it is preferable if x is between 0.05 and 0.7, y is between 0 and 0.35, z is between 0.45 and 1, and $1-y-z$ is between 0 and 0.25. For the second layer, it is preferable if q is between 0 and 0.25 and $1-r-s$ is between 0.25 and 1.

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INTERNATIONAL SEARCH REPORT

International Application No.

PCT/US 99/28576

A. CLASSIFICATION OF SUBJECT MATTER

IPC 7 H01S5/32 H01S5/34 H01L33/00 H01S5/183 H01L31/00

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 H01S

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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Y	column 2, line 37-42; figures 4-10	4, 5, 30-44
A	column 3, line 33-60	10, 12-15, 20-22, 24
	column 6, line 52 -column 7, line 14 column 8, line 9-62 column 10, line 34-50 --- -/-	



Further documents are listed in the continuation of box C.



Patent family members are listed in annex.

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International Application No

PCT/US 99/28576

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

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